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THE UNITED STATES PATENT AND TRADEMARK OFFICE  
BEFORE THE BOARD OF PATENT APPEALS AND INTERFERENCES

In re application of

MICHAEL SHU-HUAN WANG ET AL.

Serial No. 10/718,921 (TI-34402)

Filed November 21, 2003

For: CHEMICAL MECHANICAL POLISHING APPARATUS AND METHOD TO  
MINIMIZE SLURRY ACCUMULATION AND SCRATCH EXCURSIONS

Art Unit 3723

Examiner Shantese L. McDonald

Customer No. 23494

Mail Stop Appeal Brief-Patents  
Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

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1-2-09

Jav M. Cantor, Reg. No. 19.906

Sir:

**SUPPLEMENT TO BRIEF ON APPEAL**

In accordance with the requirements of the ORDER dated December 125, 2008, attached hereto is a revised CLAIMS APPENDIX.

Respectfully submitted,

Jay M. Cantor  
Reg. No. 19906  
(301) 424-0355  
(972)917-5293

## **CLAIMS APPENDIX**

The claims on appeal read as follows:

12. A method for cleaning a polishing pad in a chemical mechanical polishing system, comprising the steps:

rotating said polishing pad having a polishing surface about a center axis, said center axis being substantially perpendicular to the polishing surface of said polishing pad; and

dispensing a wash material to said polishing pad all along an area from the circumference of said polishing surface to the most center portion of said polishing surface about and including said axis while said polishing pad is rotating.

13. The method of Claim 12, further including providing a spray arm for dispensing said wash material and providing a spray extension which is coupled to the dispensing arm of said chemical mechanical polishing system for dispensing said wash material directly to the most center portion of said polishing surface about and including said axis.

14. The method of Claim 12, further comprising dispensing said de-ionized water solution directly to the most center portion of the polishing surface about said axis following polishing of a semiconductor wafer.